

### KTB1366 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 2 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : -3 A

Collector-base voltage

$V_{(BR)CBO}$ : -60 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60V, I_E=0$			-100	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-7V, I_C=0$			-100	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-0.5A$	60		200	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-3A$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-5V, I_C=-0.5A$			-1	V
Transition frequency	$f_T$	$V_{CE}=-5V, I_C=-0.5A$		9		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10V, I_E=0, f=1MHz$		150		pF
Fall time	$t_f$	$I_C=-2A, I_{B1}=-I_{B2}=-0.2A$		0.5		$\mu s$
Storage time	$t_s$	$V_{CC}=-30V$		1.7		$\mu s$

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	60-120	100-200
Marking		